

FOR USE BY ELECTRICIANS OVERSEAS :

最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T _b =25°C)					電 気 的 特 性 (T _b =25°C)										外 形	備 考
				V _{ceo} (V)	V _{ceo} (V)	I _c (mA)	P _c (mW)	T _j (°C)	I _{ceo} 最大値 (μA)	直流又はパルスI _{BE}		バイアス		h _{FE}	h _{ie} h _{ie} * (Ω)	h _{re} h _{re} * (×10 ⁻⁴)	h _{oe} h _{oe} * (μS)	f _{αb} f _r * (Mc)		
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{CBO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE}, I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB}, I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9 f_{αb} OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_r.
- 10 C_{ob} AND r_{bb'} OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN r_{bb'} COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
- 11 OUTLINE
- 12 REMARKS

:とコンプリ: COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電 気 的 特 性 (T _a = 25°C)											外形	備考									
				V _{CEO} (V)	V _{EB0} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CEO} 最大値 (μA)	V _{CE} (V)	直流又はパルス h _{FE}	バイアス	V _{CE} (V)	I _E (mA)	h _{FE}	h _{ie} h _{ie} * (Ω)	h _{re} h _{re} * (×10 ⁻⁴)	h _{oe} h _{oe} * (μΩ)	f _{αB} f _T * (Mc)			C _{ob} (pF)	r _{bb} h _{ie} (real)* (Ω)							
2SC1811	ソニー	RF	Si.E	240	5	100	750	120	0.2	100	150	5	3	10	-20	h _{ie} = 8dB (f=100MHz)									2.4	C _T 75pS 45pS	259	2SA896 とコンパリ		
" 1812	"	"	"	22	3	20	210	100	0.2	15	80	10	3	10	-3	NF=3.7dB (f=800MHz, V _{CE} =10V, I _C =3mA)								1100*	0.75	C _T 80pS 3.5pS	305A	フェワード AGC		
" 1813	"	"	Si.E PaMe	50	5	500	500	120	0.2	49	200	2	100	10	-10										100*	8	C _T 75pS 110pS	138D		
" 1814																														
" 1815	東芝	AF	Si.E	60	5	150	400	125	0.1	60	70~700	6	2	10	-1	NF=1dB (f=1kHz, 6V, 0.1mA)									>80*	2	50	138	2SA1015 とコンパリ	
" 1816	ソニー	RF. PA	Si.E PaMe	100	6	4A	16W (T _C =25°C)	150	1	50	100	2	100	10	-100	P _o = 6W (f=27MHz, V _{CE} =12V, P _i =0.4W)									140*	45	C _T 75pS 35pS	268		
" 1817	"	PA	Si.E	45	4	5A	25W (T _C =25°C)	150	2	40	60	2	100	10	-1A	P _o = 20W (f=27MHz, V _{CE} =12V, P _i =1W)									250*	80		268		
* " 1818	松下	PA	Si.EMe	130	5	7A	100W (T _C =25°C)	150	500	70	150	5	7A	10	-500										7*	400	10	102		
" 1819	"	"	Si.TP	300	5	100	15W (T _C =25°C)	150	10	300	100	10	30	30	-20										100*	4.5	15	268		
" 1820	富士通	RF. PA	Si.EP	55	3.5	500	3W (T _C =25°C)	175	100	20	50	5	200			P _o = 1.6W (f=175MHz)										4		84B		
" 1821	"	"	"	55	3.5	500	7W (T _C =25°C)	175	100	20	50	5	200			P _o = 4W (f=470MHz)										4.5		246		
" 1822	"	"	"	55	3.5	1A	12W (T _C =25°C)	175	200	20	50	5	500			P _o = 7.5W (f=470MHz)										7		246		
" 1823	"	"	"	55	3.5	2A	25W (T _C =25°C)	175	400	20	50	5	1A			P _o = 15W (f=470MHz)										12		246		
" 1824	"	"	"	55	3.5	4A	40W (T _C =25°C)	175	800	20	50	5	3A			P _o = 30W (f=470MHz)										23		246		
" 1825	"	"	"	55	3.5	8A	75W (T _C =25°C)	175	1.6mA	20	50	5	6A			P _o = 55W (f=470MHz)										45				
" 1826	サンケン	PA	Si.TMe	80	6	4A	30W (T _C =25°C)	150	1mA	80	100	4	1A	12	-200										10*	40	20*	298		
" 1827	"	"	"	100	6	4A	30W (T _C =25°C)	150	1mA	100	100	4	1A	12	-200										10*	40	20*	298		
" 1828	"	"	"	800	6	1A	40W (T _C =25°C)	150	100	800	70	10	200	10	-100										7*	20	12*	99		
" 1829	"	"	"	200	6	5A	100W (T _C =25°C)	150	1mA	200	1000	4	1A	12	-500										15*	50	100*	102		
" 1830	"	"	"	140	7	15A	150W (T _C =25°C)	150	100	140	>500	2	8A	12	-500										10*			102	ゲーリントン	
" 1831	"	"	"	90	6	8A	100W (T _C =25°C)	150	1mA	90	1000	4	1A	12	-500										10*	100	40*	102	ゲーリントン	
" 1832	"	"	"	500	6	15A	150W (T _C =25°C)	150	100	500	300	2	10A	12	-500										7*	130	40*	102	ゲーリントン	
" 1833	日電	RF.SW	Si.E	60	8	200	300	150	0.1	40	160	1	10	10	-10	t _{on} = 45nS t _{off} = 250nS t _{sig} = 190nS									300*	3.5		138		
" 1834	"	"	"	40	5	200	300	150	0.1	30	120	1	10	10	-10	t _{on} < 20nS, t _{off} < 40nS t _{sig} < 20nS									500*	4	120	138		
" 1835																														
" 1836																														
* " 1837	富士通	PA	Si.EP	35	3.5	600	7.5W (T _C =25°C)	175	400	20	50	5	200			P _o = 1W (f=2GHz, V _{CE} =18V, P _i =0.2W)													166	
* " 1838	"	"	"	35	3.5	1.5A	15W (T _C =25°C)	175	1mA	20	50	5	500			P _o = 3W (f=2GHz, V _{CE} =18V, P _i =1W)													166	
" 1839																														
" 1840	日電	AF	Si.E	40	5	100	500	125	0.05	40	400	6	1	6	-1										100*	< 8		138		